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Effect of sintering aids on the densification and electrical properties of SiO<sub>2</sub> -

containing Ce<sub>0.8</sub>Sm<sub>0.2</sub>O<sub>1.9</sub> ceramic

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**Abstract:** 

In this work, five different metal-oxide additives (metal=Ba, Co, Fe, Li, and Mn) were

examined as sintering aids and SiO<sub>2</sub> impurity scavengers for Ce<sub>0.8</sub>Sm<sub>0.2</sub>O<sub>1.9</sub> (SDC). 2

mol% additives were loaded into the SDC with ~150 ppm (moderately impure) and

~2000 ppm (highly impure) SiO<sub>2</sub>. Ba-, Co-, Fe- and Mn-oxides showed comparative

sintering-aid effect on both moderately- and highly-impure SDC specimens, but the

sintering-assisting effect of Li-oxide was completely neutralized in highly impure SDC.

Regarding electrical property, the deleterious effect of 2000 ppm SiO<sub>2</sub> impurity on the

grain-boundary conduction of SDC can be effectively alleviated by adding Ba-, Co-,

Fe-, or Mn-oxides. Microstructure analysis revealed that Ba-oxide reacted directly with

SiO<sub>2</sub> and consequently enhanced grain-boundary conduction. By contrast, with the

addition of Co-, Fe-, and Mn-oxides, the improved grain-boundary conductions of

impure SDC were related to the scavenging reactions between Si, Ca (another original

impurity) and Sm components.

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